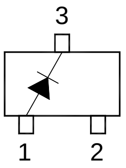
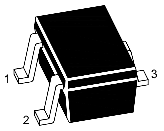
# SDB127W

## Silicon Epitaxial Planar Schottky Barrier Diode

**Features**

- Low forward voltage
- Allowing high density mounting





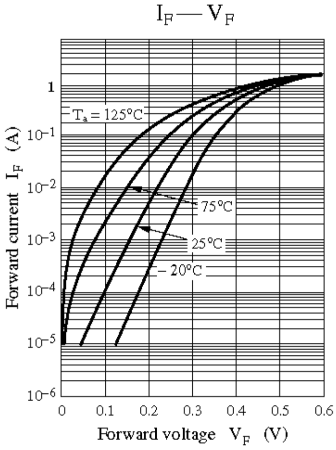
SOT-323 Plastic Package
Marking Code: **YR**

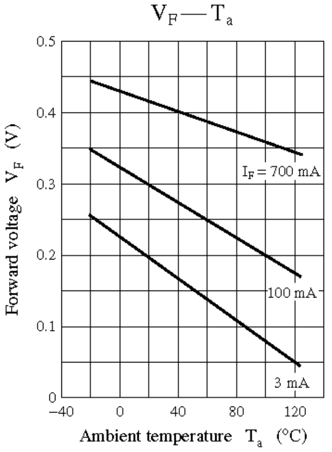
### Absolute Maximum Ratings ($T_a$ = 25℃)

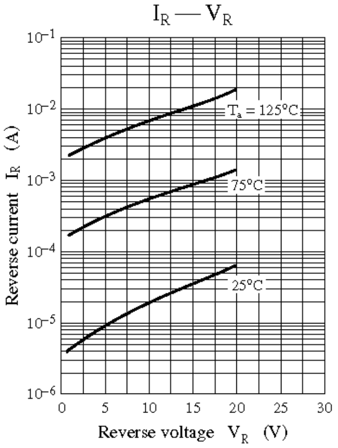
| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Repetitive Peak Reverse Voltage | $V_{RRM}$ | 25 | V |
| Reverse Voltage | $V_R$ | 20 | V |
| Average Forward Current | $I_{F(AV)}$ | 700 | mA |
| Non-repetitive Peak Forward Surge Current (t = 8.3 ms) | $I_{FSM}$ | 2 | A |
| Junction Temperature | $T_J$ | 125 | ℃ |
| Storage Temperature Range | $T_{stg}$ | - 55 to + 125 | ℃ |

### Characteristics at $T_a$ = 25℃

| Parameter | Symbol | Min. | Max. | Unit |
|---|---|---|---|---|
| Forward Voltage<br>at $I_F$ = 700 mA | $V_F$ | - | 0.45 | V |
| Reverse Current<br>at $V_R$ = 20 V | $I_R$ | - | 200 | µA |
| Reverse Breakdown Voltage<br>at $I_R$ = 600 µA | $V_{(BR)R}$ | 25 | - | V |
| Junction Capacitance<br>at $V_R$ = 0, f = 1 MHz | $C_J$ | - | 100 | pF |


$I_F$ — $V_F$


$V_F$ — $T_a$


$I_R$ — $V_R$